

FORM HDP-1449 (Based on Form PTO-1449)

**PATENT AND TRADEMARK OFFICE  
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Sheet 1 of 2

ATTORNEY DOCKET No.

5077-000075/DVA

SERIAL No.

APPLICANT

Toshiya Yokogawa et al.

FILING DATE

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**U.S. PATENT DOCUMENTS**

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.	TTN	6,483,100	11/2002	Williams et al.		
2.		5,091,759	02/1992	Shih et al.		
3.		5,284,782	02/1994	Jeong et al.		
4.		5,463,978	11/1995	Larkin et al.		
5.		5,492,857	02/1996	Reedy et al.		
6.		6,057,566	02/2000	Eisenbeiser et al.		
7.		5,013,685	05/1991	Chiu et al.		
8.		5,324,682	06/1994	Tserng		
9.		6,025,613	02/2000	Bito et al.		
10.		6,258,616	06/2001	Cunningham et al.		
11.		5,488,237	01/1996	Kuwata		
12.	TTN	6,380,569	04/2002	Chang et al.		

**FOREIGN PATENT DOCUMENTS**

Ref. D sig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.	TTN	05013446 A	01/22/1993	Japan		Partial	
2.	TTN	0 555 886 A2	08/18/1993	Europe			

Examiner:

Date Considered:

6/15/04

EXAMINER: PI as initial citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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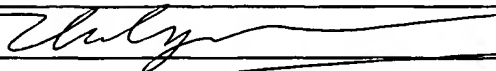
FILING DATE

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**OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)**

R f. Desig.	Examiner's Initials	
1.	TTN	Wen-Chau Liu et al.; "Application of $\delta$ -doped Wide-Gap Collector Structure for High-Breakdown and Low-Offset voltage Transistors"; American Institute of Physics; September 7, 1998.
2.	TTN	Asen Asenov et al.; "Suppression of Random Dopant-Induced Threshold Voltage Fluctuations in Sub-0.1- $\mu$ m MOSFET's with Epitaxial and $\delta$ -Doped Channels"; IEEE Transaction on Electron Devices; Vol. 46, No. 8; August 1999.
3.	TTN	Hata (US patent Application Publication 2002/0008242 A) US class 257/79

Examiner:



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